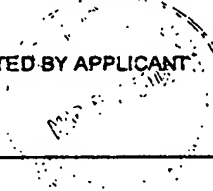
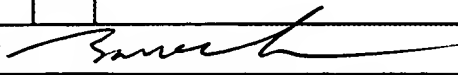


Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 245469US2DIV		SERIAL NO. 10/716,556	
LIST OF REFERENCES CITED BY APPLICANT 				APPLICANT Tadashi IGUCHI, et al.			
				FILING DATE November 20, 2003		GROUP 2813	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
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	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO						
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
✓	AW	K. SHIMIZU, et al., "A Novel High-Density 5F ² NAND STI Cell Technology Suitable for 256Mbit and 1Gbit Flash Memories", Microelectronics Engineering Laboratory, IEDM 97-271-274					
✓	AX	Kenichi IMAMIYA, et al., "A 130-mm ² , 256-Mbit NAND Flash with Shallow Trench Isolation Technology", IEEE Journal of Solid-State Circuits, vol. 34, no. 11, November 1999, pages 1536-1543					
	AY						
	AZ						<input type="checkbox"/> Additional References sheet(s) attached
Examiner 					Date Considered 11/1/05		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							